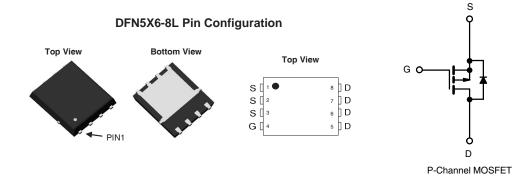


P-Channel 100-V (D-S) Super Junction MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	R _{DS(on)} (mΩ)(Typ.)	I _D (A) ^a	Q _g (Typ.)			
-100	18 at V _{GS} = - 10 V	-65	86 nC			
-100	22 at V _{GS} = - 4.5 V	-05				

FEATURES

- DT-SJ Power MOSFET
- 100 % R_g and UIS Tested
- Low R_{DS(ON)}
- **APPLICATIONS**
- Notebook AC-in load switch
- Battery protection charge/discharge



ABSOLUTE MAXIMUM RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)					
PARAMETER	SYMBOL	Limit	UNIT		
Drain-Source Voltage		V _{DS}	-100	V	
Gate-Source Voltage		V _{GS}	±20		
Continuous Drain Current (T,I = 150 °C) ^a	T _C = 25 °C	1	-65		
Continuous Drain Current (1) = 150°C)"	T _C = 100 °C	I _D	-43	А	
Pulsed Drain Current ^b		I _{DM}	-260		
Single Pulse Avalanche Energy		E _{AS}	335	mJ	
Maximum Power Dissipation ^c	T _C = 25 °C	PD	156 ^{b,c}	- w	
	T _C = 100 °C	۳D	62.4 ^{b,c}		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to + 150	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	LIMIT	UNIT		
Junction-to-Ambient (PCB Mount) ^d	R _{thJA}	50	°C/W		
Junction-to-Case (Drain)	R _{thJC}	0.8	C/W		

Notes

a. Calculated continuous current based on maximum allowablejunction temperature.

b. Repetitive rating; pulse width limited by max. junction temperature.

- c. Pd is based on max. junction temperature, using junction-case thermal resistance.
- d. The value of ReuA is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with Ta=25 °C.

SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static	1			1	1		
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, \text{ I}_{D} = -250 \mu\text{A}$	-100	-	-	V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = -250 \ \mu A$	-1	-	-3		
Gate-Body Leakage	I _{GSS}	$V_{DS}=0~V,~V_{GS}=\pm~20~V$	-	-	± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -100 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	-	-	-1	μA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \geq -10 \ V, \ V_{GS} = -10 \ V$	-70	-	-	А	
Drain-Source On-State Resistance ^a	Brach	$V_{GS} = -10 \text{ V}, \text{ I}_{D} = -20 \text{ A}$	-	18	22	mΩ	
	R _{DS(on)}	V_{GS} = -4.5 V, I_D = -20 A	-	22	30		
Forward Transconductance ^a	9 _{fs}	$V_{DS} = -5 \text{ V}, \text{ I}_{D} = -20 \text{ A}$	-	35	-	S	
Dynamic ^b							
Input Capacitance	C _{iss}		-	1910	-	pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 V, V_{DS} = -50 V, f = 1 MHz$	-	377	-		
Reverse Transfer Capacitance	C _{rss}		-	15	-		
Total Gate Charge ^c	Qg		-	86	-	nC	
Gate-Source Charge ^c	Q _{gs}	V_{DS} = -50 V, V_{GS} = -10 V, I_{D} = -20 A	-	16	-		
Gate-Drain Charge ^c	Q _{gd}		-	10	-		
Gate Resistance	Rg	f = 1 MHz	-	40	-	Ω	
Turn-On Delay Time ^c	t _{d(on)}		-	15	-		
Rise Time ^c	t _r	V _{DD} = -50 V, I _D = -20 A	-	20	-		
Turn-Off Delay Time ^c	t _{d(off)}	V_{GS} = -10 V, R_g = 3 Ω	-	35	-	ns	
Fall Time ^c	t _f		-	18	-		
Drain-Source Body Diode Ratings an	nd Characteris	stics ^b (T _C = 25 °C)					
Continuous Source Current	I _S	T _C = 25 °C	-	-	-65	А	
Pulsed Source Current	I _{SM}		-	-	-260	А	
Forward Voltage ^a	V _{SD}	$I_{S} = -20 \text{ A}, V_{GS} = 0 \text{ V}$	-	-	-1.2	V	
Reverse Recovery Time	t _{rr}		-	35	-	ns	
Reverse Recovery Charge	Q _{rr}	I _S = -20 A, di/dt = -100 A/μs	-	150	-	nC	

Notes

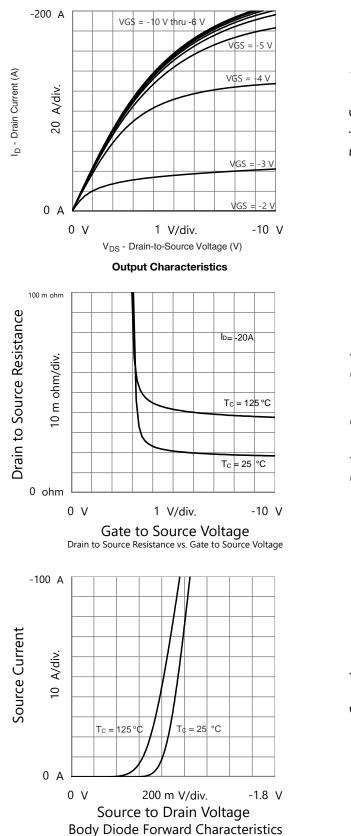
a. Pulse test; pulse width $\leq 300~\mu\text{s},$ duty cycle $\leq 2~\%.$

b. Guaranteed by design, not subject to production testing.

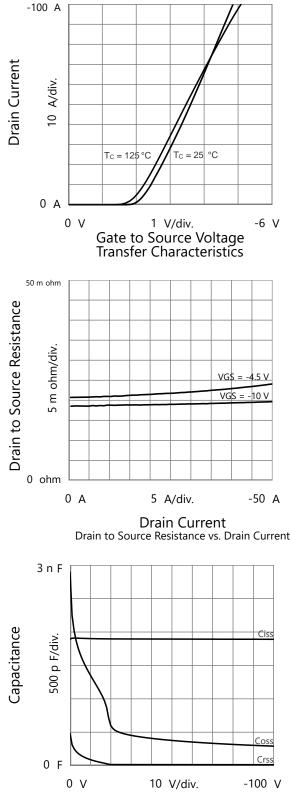
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



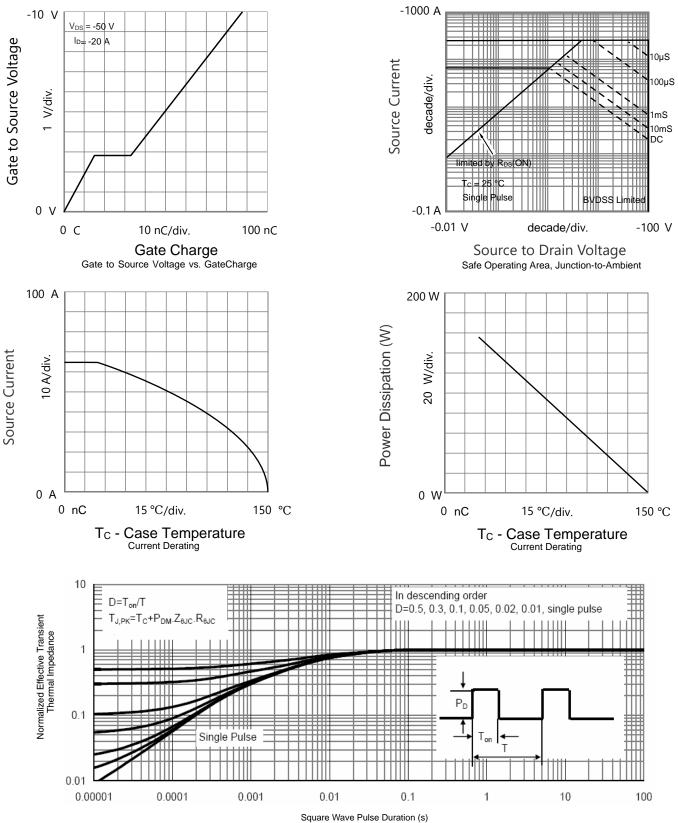


TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Drain to Source Voltage Capacitances



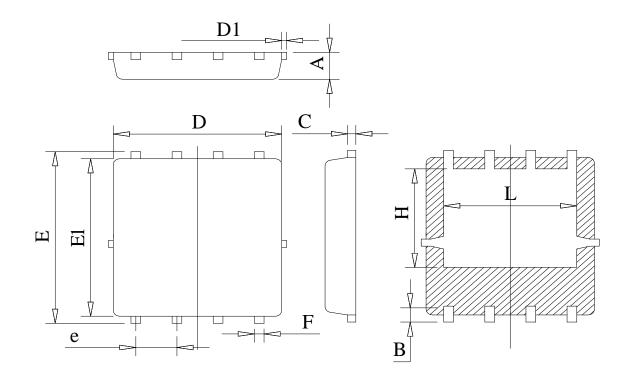


TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





DFN5X6-8L PACKAGE OUTLINE



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

Unit : mm			
Symbol	Min	Тур	Max
А	0.78	0.95	1.12
В	0.45	0.58	0.78
С	0.18	0.254	0.36
D	4.70	5.20	5.45
D1			0.18
Е	5.85	6.05	6.25
E1	5.38	5.55	5.98
e	1.15	1.27	1.40
F	0.18	0.30	0.52
Н	3.25	3.47	3.70
L	3.75	4.00	4.25



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